

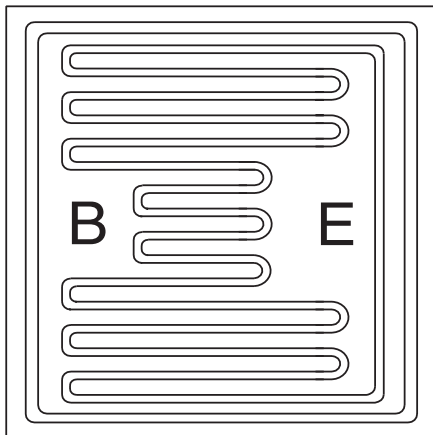
PROCESS CP714
Small Signal Transistor
PNP - High Current Transistor Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

| | |
|--------------------------|------------------|
| Process | EPITAXIAL PLANAR |
| Die Size | 40 x 40 MILS |
| Die Thickness | 9.0 MILS |
| Base Bonding Pad Area | 7.9 x 8.7 MILS |
| Emitter Bonding Pad Area | 9.0 x 14 MILS |
| Top Side Metalization | Al - 30,000Å |
| Back Side Metalization | Au - 18,000Å |

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

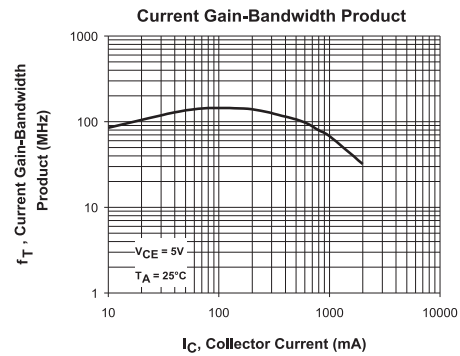
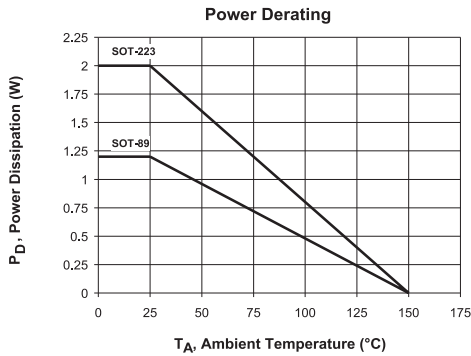
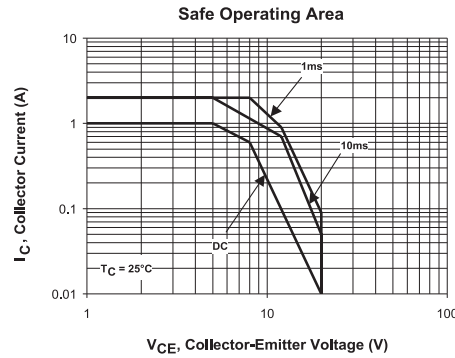
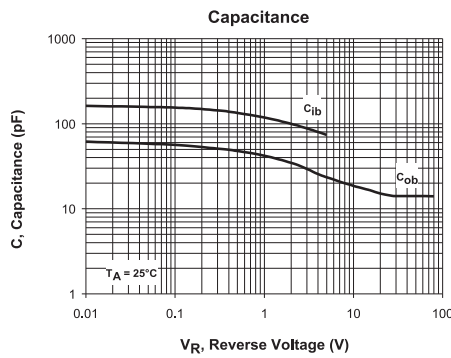
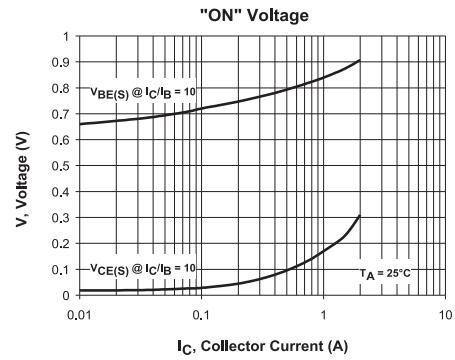
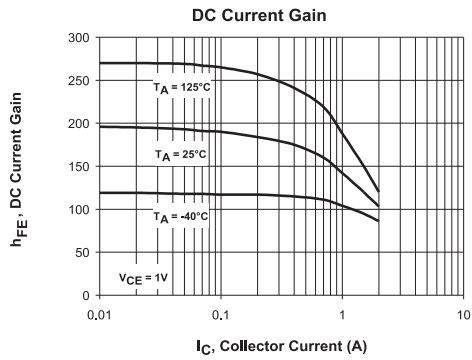
7,070

PRINCIPAL DEVICE TYPES

CBCP69
CBCX69
CZT751
MPS750
MPS751

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R2 (1-August 2002)



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